

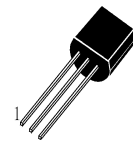
■ APPLICATIONS

HIGH CURRENT APPLICATIONS.

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	—Storage Temperature -55~150°C
T _j	—Junction Temperature 150°C
P _C	—Collector Dissipation 600mW
V _{CBO}	—Collector-Base Voltage 35V
V _{CEO}	—Collector-Emitter Voltage 30V
V _{EBO}	—Emitter-Base Voltage 5V
I _C	—Collector Current 800mA

TO-92



1—Emitter, E
2—Collector, C
3—Base, B

■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	35			V	I _C =100 μA, I _E =0
BVCEO	Collector-Emitter Breakdown Voltage	30			V	I _C =10mA, I _B =0
BVEBO	Emitter-Base Breakdown Voltage	5			V	I _E =1mA, I _C =0
HFE (1)	DC Current Gain	100		320		V _{CE} =1V, I _C =100mA
HFE (2)	DC Current Gain	35				V _{CE} =1V, I _C =700mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage			0.5	V	I _C =500mA, I _B =20mA
V _{BE}	Base-Emitter Voltage	0.5		0.8	V	V _{CE} =1V, I _C =10mA
I _{CBO}	Collector Cut-off Current			100	nA	V _{CB} =35V, I _E =0
I _{EBO}	Emitter Cut-off Current			100	nA	V _{EB} =5V, I _C =0
f _T	Current Gain-Bandwidth Product		120		MHz	V _{CE} =5V, I _C =10mA
C _{ob}	Output Capacitance		13		pF	V _{CB} =10V, I _E =0, f=1MHz

■ HFE Classification

O

Y

100—200

160—320